

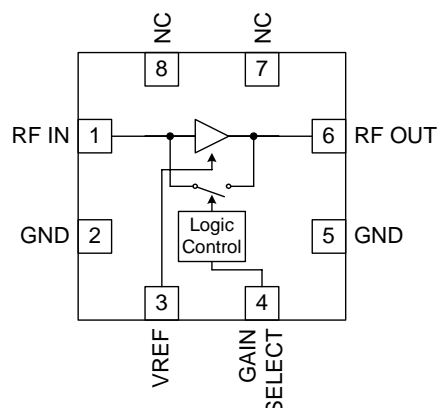
RoHS Compliant & Pb-Free Product
Package Style: QFN, 8-Pin, 2.2mmx2.2mmx0.6mm

Features

- Low Noise and High Intercept Point
- Adjustable Bias Current
- Power Down Control
- Low Insertion Loss Bypass Feature
- 1.8V to 4V Operation (See Note: Page 2)
- 800MHz to 3.8GHz Operation
- ESD Class 1B

Applications

- WLAN LNA with Bypass Feature
- CDMA PCS LNA with Bypass Feature
- GPS LNA with Bypass Feature
- General Purpose Amplification
- WiMAX LNA with Bypass Function
- CDMA 800 LNA



Functional Block Diagram

Product Description

The RF2374 is a switchable low noise amplifier with a high dynamic range designed for digital cellular and WLAN applications. The device functions as an outstanding front end low noise amplifier with I_{CC} as low as 3mA. The bias current may be set externally. The IC is featured in a 2.2mmx2.2mmx0.6mm module-compatible plastic package.

Ordering Information

RF2374	3V Low Noise Amplifier
RF2374 PCK-410	Fully Assembled Evaluation Board, 2.3GHz to 3.8GHz with standard tune
RF2374 PCK-411	Fully Assembled Evaluation Board, 1.5GHz to 2.2GHz with standard tune

Optimum Technology Matching® Applied

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|--|--------------------------------------|-------------------------------------|-----------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

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Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.5 to +6.0	V _{DC}
Input RF Level	+5 (see note)	dBm
Current Drain, I _{CC}	32	mA
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C

NOTE: Exceeding any one or a combination of the above maximum rating limits may cause permanent damage. Input RF transients to +15dBm will not harm the device. For sustained operation at inputs $\geq +5$ dBm, a small dropping resistor is recommended in series with the V_{CC} in order to limit the current due to self-biasing to <32mA.



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Operating Range					T _{AMB} = +25 °C, V _{CC} = 3.0V
Frequency Range	800		4000	MHz	
WiBRO/WLAN/WiMAX Low Noise Amplifier					
Frequency	2300		2700	MHz	
HIGH GAIN MODE					Gain Select < 0.8V, V _{REF} = 3V, T = +25 °C
Gain	13.5	14.5		dB	
Noise Figure		1.3	1.5	dB	
Input IP3	+7	+9		dBm	IIP3 will improve if I _{CC} is raised above 7mA.
IP1dB	0			dBm	
Current Drain		7		mA	
BYPASS MODE (Low Gain)					Gain Select \geq 1.6V
Gain	-4.0	-3.0	-2.0	dB	Note: Bypass mode insertion loss will degrade gradually as V _{CC} goes below 2.7V.
Input IP3	+20	+21		dBm	
Current Drain		2.8	3.0	mA	Current drain includes I _{CC} + I _{REF}
GPS Low Noise Amplifier					
Frequency		1575		MHz	
Gain		17.5		dB	I _{CC} = 6.5mA, I _{CC} + I _{REF} = 7.5mA
Noise Figure		1.2		dB	
Input IP3		+7.0		dBm	
WiMAX Low Noise Amplifier					
Frequency	3100	3500	3800	MHz	I _{CC} = 7mA
Gain		11.0		dB	
Noise Figure		1.6		dB	
Input IP3		+10.0		dBm	IIP3 will improve if I _{CC} is raised above 7mA.
BYPASS MODE (Low Gain)					
Gain		-3.0	-2.5	dB	
Input IP3	20.5	22.0		dBm	

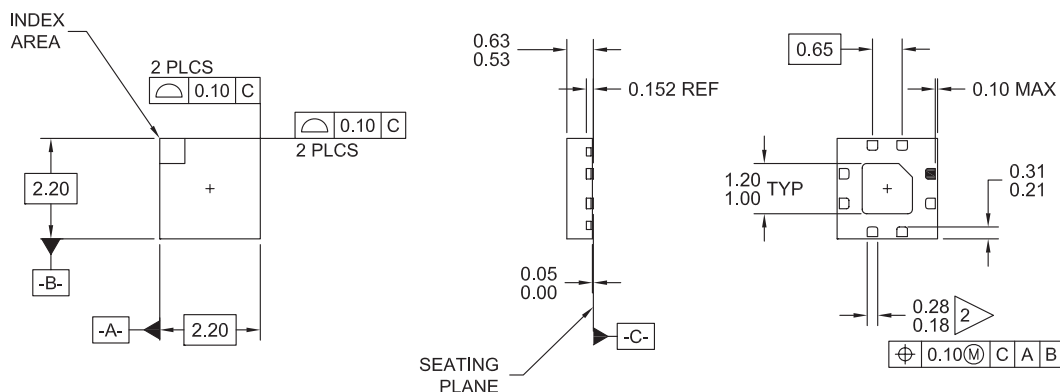
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
CDMA Low Noise Amplifier					
HIGH GAIN MODE					
Frequency	869		894	MHz	
Gain		19		dB	
Noise Figure		1.0		dB	
Input IP3		+2.0		dBm	IIP3 will improve if I _{CC} is raised above 7 mA.
Current Drain		7		mA	
Power Supply					
Voltage (V _{CC})		3		V	
Gain Select Low Level (High Gain Mode)			0.8	V	High Gain mode. Gain Select<0.8V, V _{REF} =3V (typical)
Gain Select High Level (Bypass Mode)	1.6			V	Low Gain mode. Gain Select≥1.6V, V _{REF} : see bias note 2
Power Down	0		5	μA	Gain Select<0.8V, V _{REF} =0V, V _{CC} =3.0V

Bias note: Due to the presence of ESD protection circuitry on the RF2374, the maximum allowable collector bias voltage (pin 6) is 4.0V. Higher supply voltages such as 5V are permissible if a series resistor is used to drop V_{CC} to \leq 4.0V for a given I_{CC} .

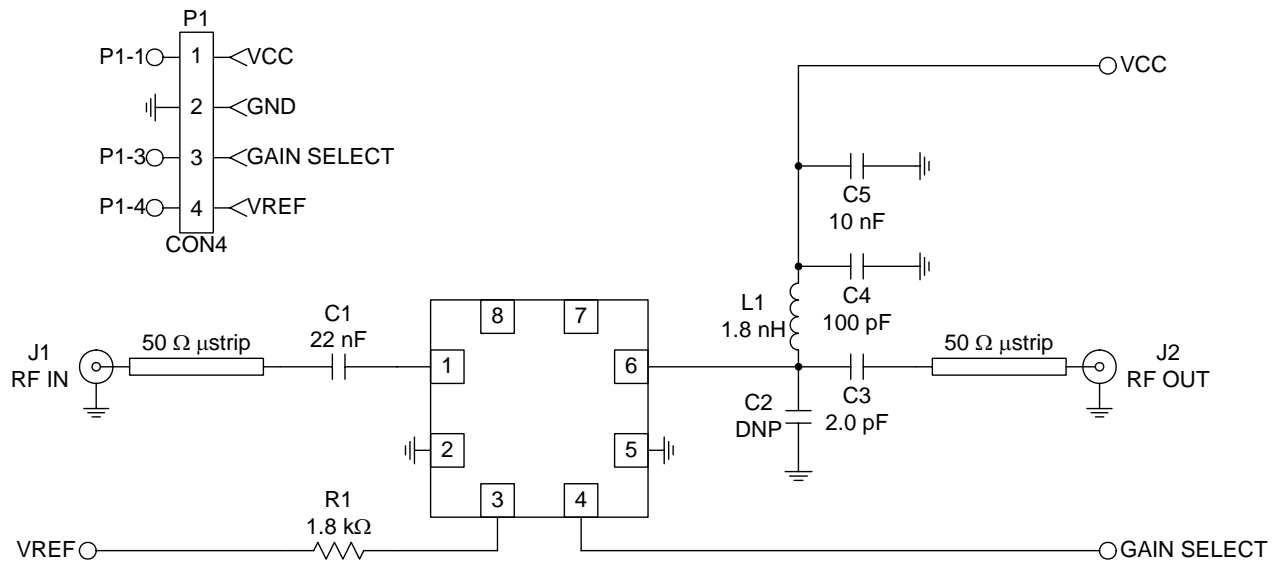
Bias note 2: In bypass mode, V_{REF} is essentially a "don't care" condition. Pulling V_{REF} low when in bypass mode does conserve the small 1mA to 2mA supplied by V_{REF} .

Pin	Function	Description	Interface Schematic
1	RF IN	RF input pin. This part is designed such that 50Ω is the optimal source impedance for best noise figure. Best noise figure is achieved with only a series capacitor on the input.	
2	GND1	Ground connection. For best performance, keep traces physically short and connect immediately to ground plane.	
3	VREF	For low noise amplifier applications, this pin is used to control the bias current. An external resistor can be used to set the bias current for any V_{BIAS} voltage. This device will have good gain and noise figure with I_{CC} as low as 3mA.	
4	GAIN SELECT	This pin selects high gain and bypass modes. Gain Select $\leq 0.8V$, high gain. Gain Select $\geq 1.6V$, low gain.	
5	GND2	See GND1.	
6	RF OUT	Amplifier output pin. This pin is an open-collector output. It must be biased to V_{CC} through a choke or matching inductor.	
7	NC	Not connected.	
8	NC	Not connected.	
Pkg Gnd	GND	This pad should be connected to the ground plane by vias directly under the device.	

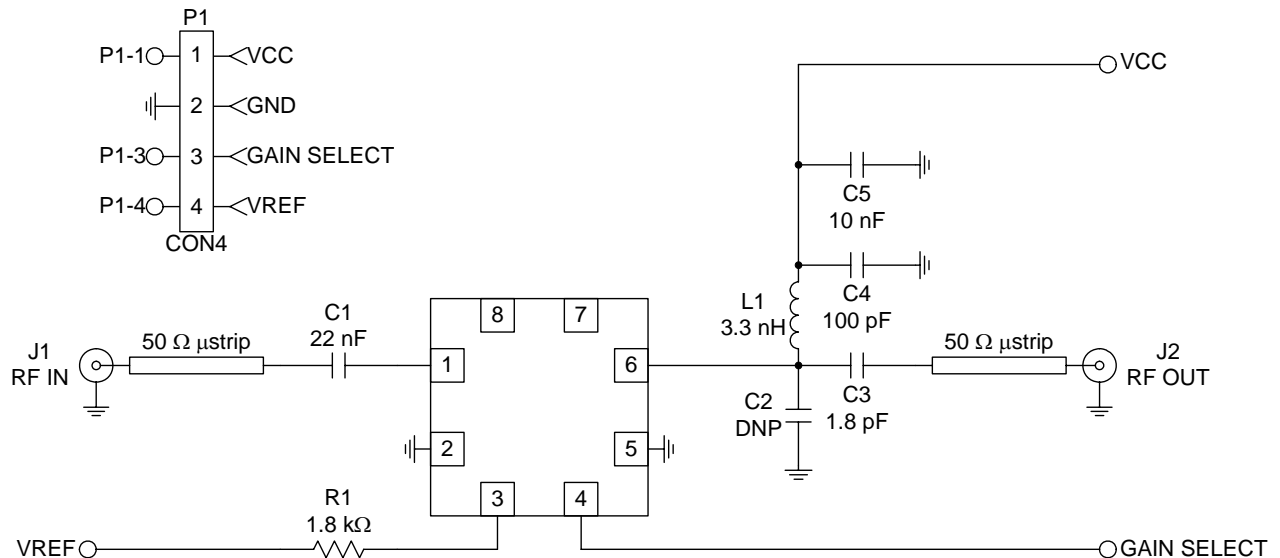
Package Drawing



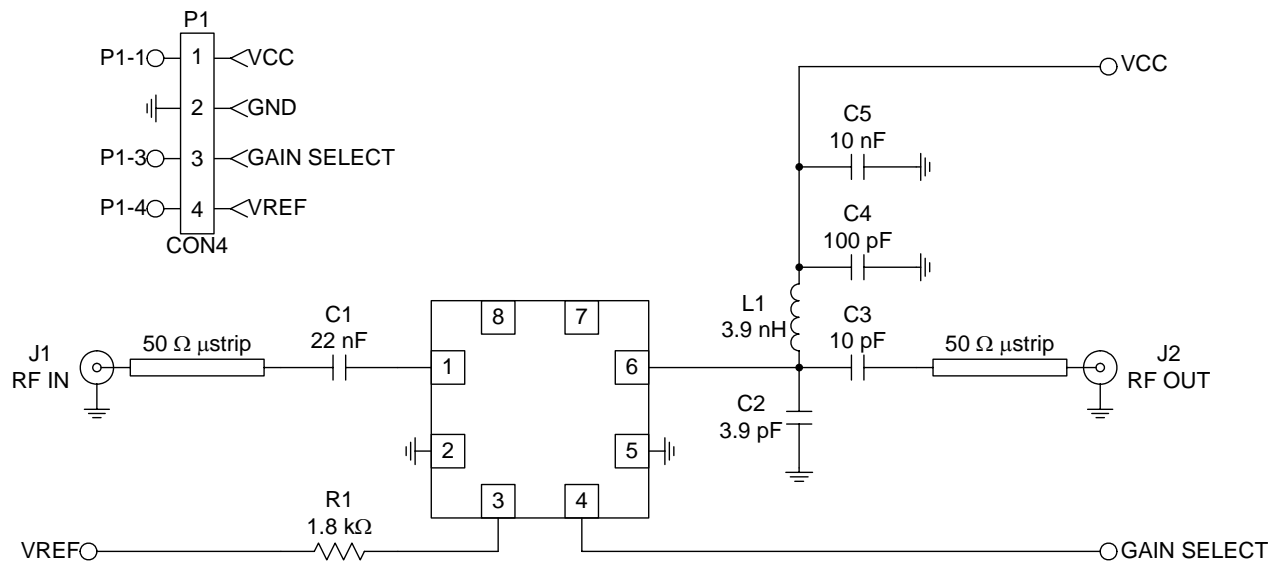
Evaluation Board Schematic WiBRO/WLAN/WiMAX (2.3GHz to 3.8GHz)



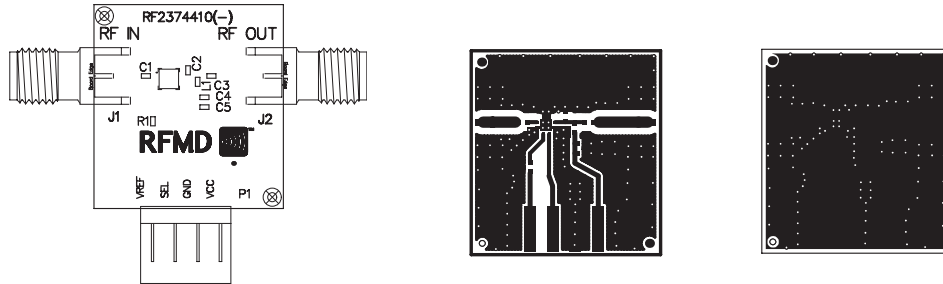
Evaluation Board Schematic GPS/PCS (1.5GHz to 2.2GHz)



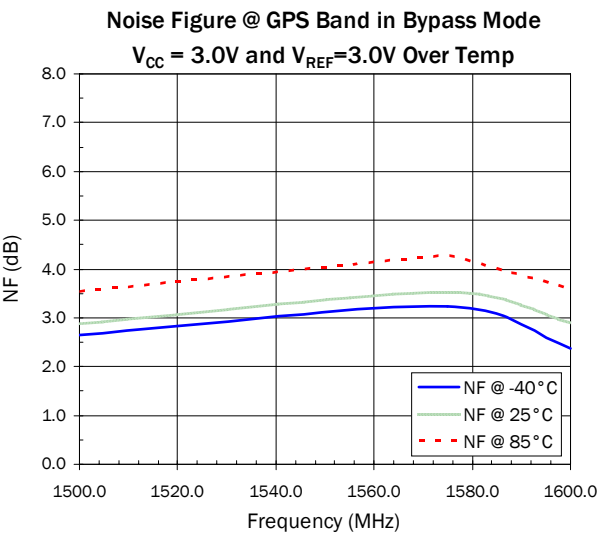
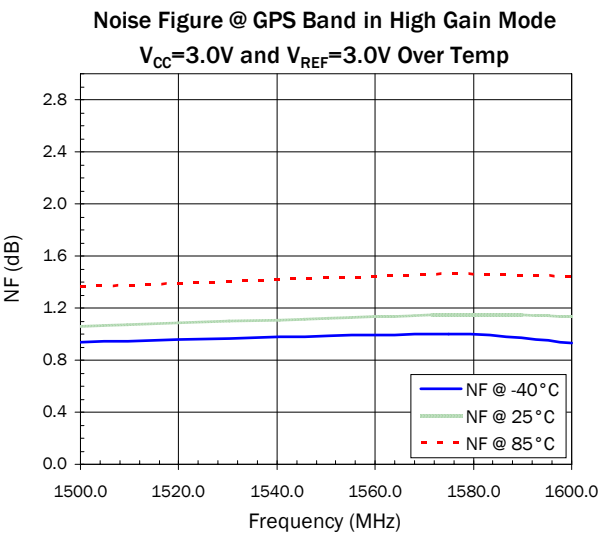
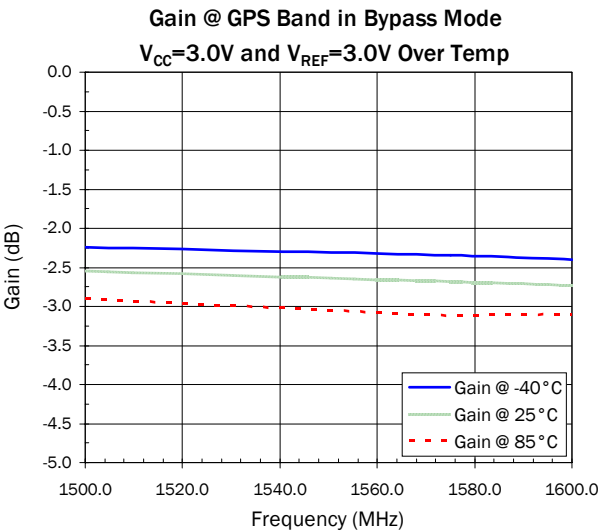
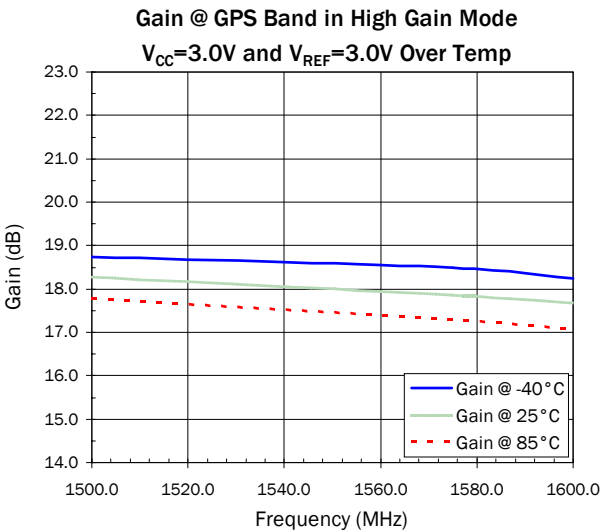
Evaluation Board Schematic - 869MHz to 894MHz

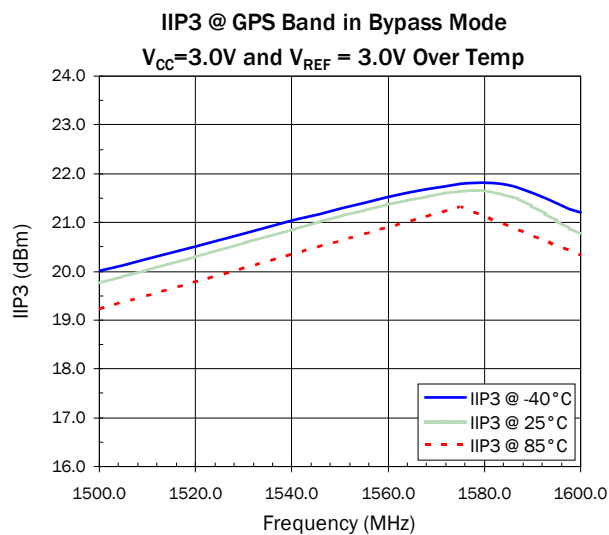
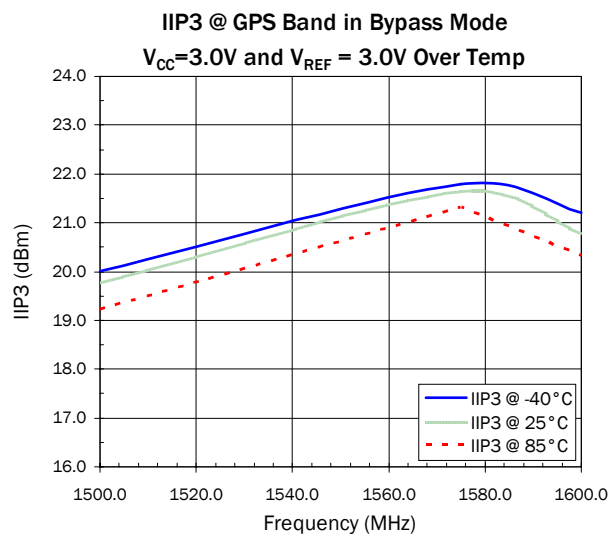
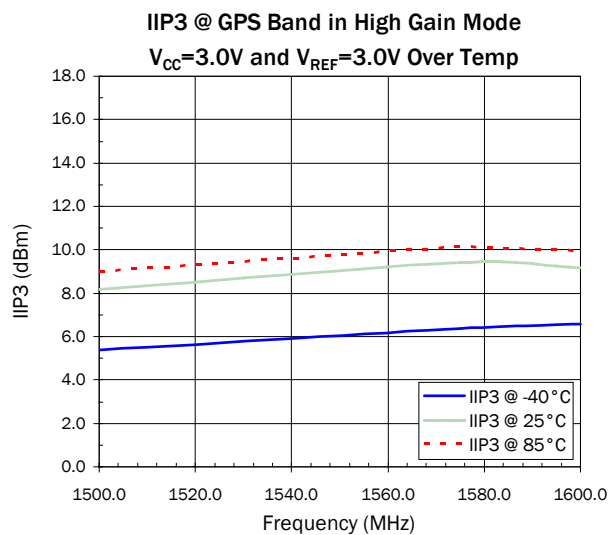


Evaluation Board Layout
Board Size 0.835" x 0.900"
Board Thickness 0.032", Board Material FR-4



GPS Band Data

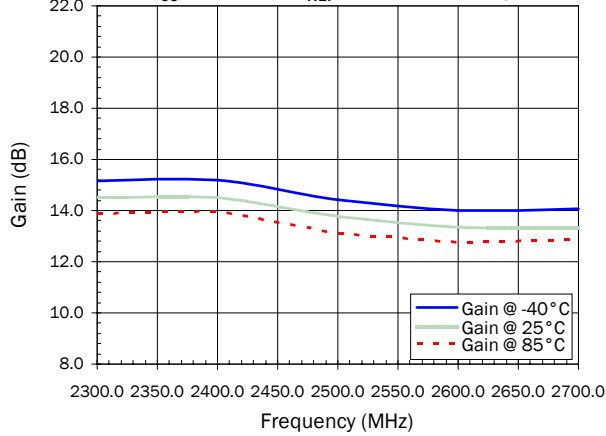




WiBRO/WLAN/WiMAX Data

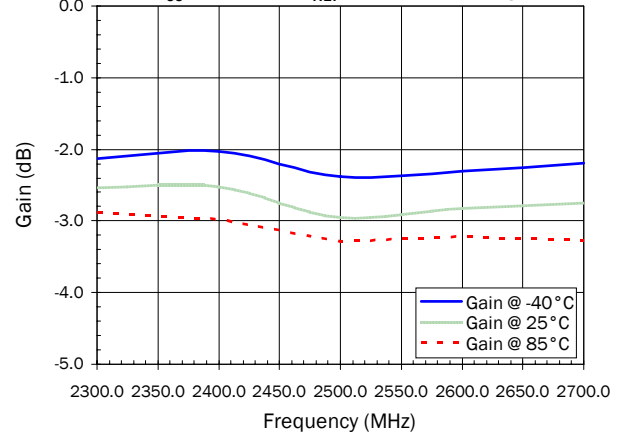
Gain @ WLAN Band in High Gain Mode

$V_{CC}=3.0V$ and $V_{REF}=3.0V$ Over Temp



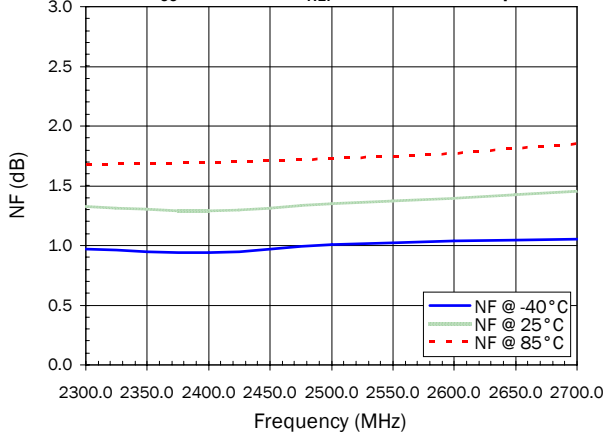
Gain @ WLAN Band in Bypass Mode

$V_{CC}=3.0V$ and $V_{REF}=3.0V$ Over Temp



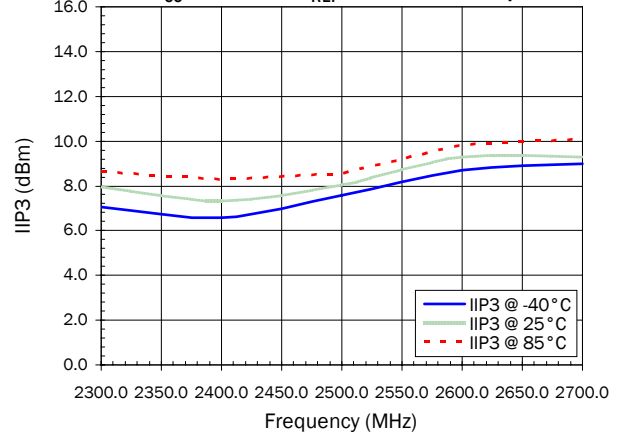
Noise Figure @ WLAN Band in High Gain Mode

$V_{CC}=3.0V$ and $V_{REF}=3.0V$ Over Temp



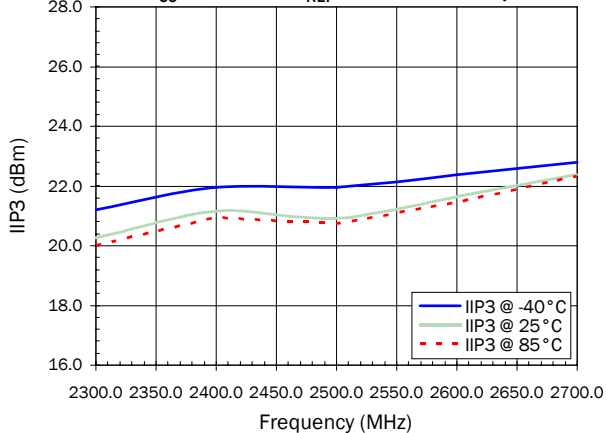
IIP3 @ WLAN Band in High Gain Mode

$V_{CC}=3.0V$ and $V_{REF}=3.0V$ Over Temp



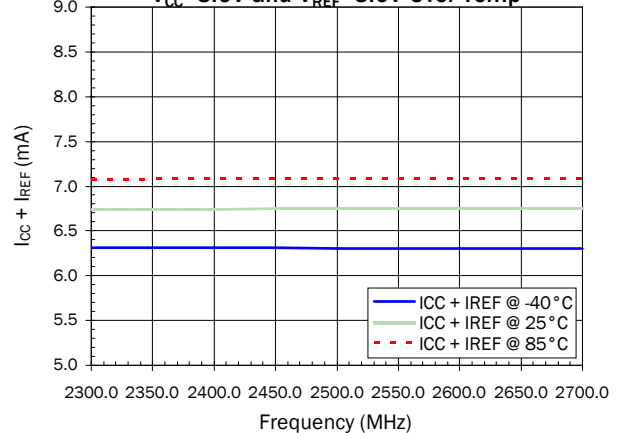
IIP3 @ WLAN Band in Bypass Mode

$V_{CC}=3.0V$ and $V_{REF}=3.0V$ Over Temp



$I_{CC} + I_{REF}$ @ WLAN Band in High Gain Mode

$V_{CC}=3.0V$ and $V_{REF}=3.0V$ Over Temp



WiMAX Data

